

NTTFS4C02N

MOSFET – Power, Single, N-Channel, μ 8FL 30 V, 170 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC-DC Converters
- Power Load Switch
- Notebook Battery Management

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit	
Drain-to-Source Voltage			V_{DSS}	30	V	
Gate-to-Source Voltage			V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	29	A	
		$T_A = 85^{\circ}\text{C}$		21		
Power Dissipation $R_{\theta JA}$ (Note 1)		$T_A = 25^{\circ}\text{C}$	P_D	2.7	W	
Continuous Drain Current $R_{\theta JA} \leq 10\text{ s}$ (Note 1)		$T_A = 25^{\circ}\text{C}$	I_D	36	A	
		$T_A = 85^{\circ}\text{C}$		26		
Power Dissipation $R_{\theta JA} \leq 10\text{ s}$ (Note 1)		$T_A = 25^{\circ}\text{C}$	P_D	4.2	W	
Continuous Drain Current $R_{\theta JA}$ (Note 2)		$T_A = 25^{\circ}\text{C}$	I_D	16	A	
		$T_A = 85^{\circ}\text{C}$		12		
Power Dissipation $R_{\theta JA}$ (Note 2)		$T_A = 25^{\circ}\text{C}$	P_D	0.83	W	
Continuous Drain Current $R_{\theta JC}$ (Note 1)		$T_C = 25^{\circ}\text{C}$	I_D	170	A	
		$T_C = 85^{\circ}\text{C}$		120		
Power Dissipation $R_{\theta JC}$ (Note 1)		$T_C = 25^{\circ}\text{C}$	P_D	91	W	
Pulsed Drain Current		$T_A = 25^{\circ}\text{C}$, $t_p = 10\text{ }\mu\text{s}$		I_{DM}	500	A
Operating Junction and Storage Temperature			T_J , T_{stg}	-55 to +150	$^{\circ}\text{C}$	
Source Current (Body Diode)			I_S	100	A	
Drain to Source dV/dt			dV/dt	6.0	V/ns	
Single Pulse Drain-to-Source Avalanche Energy ($I_L = 37\text{ A}_{pk}$) (Note 3)			E_{AS}	162	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

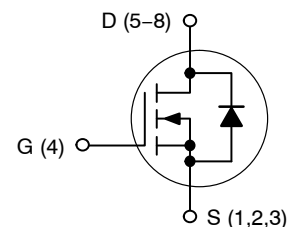


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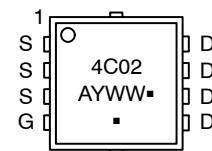
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	2.25 m Ω @ 10 V	170 A
	3.1 m Ω @ 4.5 V	

N-Channel MOSFET



WDFN8
(μ 8FL)
CASE 511AB

MARKING DIAGRAM



4C02 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTTFS4C02NTAG	WDFN8 (Pb-Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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- Surface-mounted on FR4 board using the minimum recommended pad size.
- This is the absolute maximum ratings. Parts are 100% tested at $T_J = 25^\circ\text{C}$, $V_{GS} = 10\text{ V}$, $I_L = 36\text{ A}$, $E_{AS} = 65\text{ mJ}$.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.4	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	46	
Junction-to-Ambient – Steady State (Note 5)	$R_{\theta JA}$	150	
Junction-to-Ambient – ($t \leq 10\text{ s}$) (Note 4)	$R_{\theta JA}$	30	

- Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			13.8		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$, $V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$, $V_{DS} = 30\text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 6)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	1.3	1.6	2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.0		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}$	1.9	2.25	m Ω
		$V_{GS} = 4.5\text{ V}$	$I_D = 20\text{ A}$	2.7	3.1	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}$, $I_D = 50\text{ A}$		140		S
Gate Resistance	R_G			0.9		Ω

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$, $V_{DS} = 15\text{ V}$		2980		pF
Output Capacitance	C_{OSS}			1200		
Reverse Transfer Capacitance	C_{RSS}			55		
Output Charge	Q_{OSS}	$V_{GS} = 0\text{ V}$, $V_{DD} = 15\text{ V}$		25		nC
Capacitance Ratio	C_{RSS}/C_{ISS}	$V_{GS} = 0\text{ V}$, $V_{DS} = 15\text{ V}$, $f = 1\text{ MHz}$		0.018		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}$, $V_{DS} = 15\text{ V}$; $I_D = 50\text{ A}$		20		nC
Threshold Gate Charge	$Q_{G(TH)}$			4.7		
Gate-to-Source Charge	Q_{GS}			8.5		
Gate-to-Drain Charge	Q_{GD}			4		
Gate Plateau Voltage	V_{GP}			2.8		V
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 15\text{ V}$; $I_D = 50\text{ A}$		45		nC

SWITCHING CHARACTERISTICS (Note 7)

- Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS (Note 7)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 50\text{ A}, R_G = 3.0\ \Omega$		12		ns
Rise Time	t_r			116		
Turn-Off Delay Time	$t_{d(OFF)}$			25		
Fall Time	t_f			10		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 50\text{ A}, R_G = 3.0\ \Omega$		9		ns
Rise Time	t_r			102		
Turn-Off Delay Time	$t_{d(OFF)}$			33		
Fall Time	t_f			6		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 20 A	T _J = 25°C		0.8	1.1	V
			T _J = 125°C		0.6		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 50 A			42		ns
Charge Time	t _a				21		
Discharge Time	t _b				21		
Reverse Recovery Charge	Q _{RR}				28		nC

6. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

7. Switching characteristics are independent of operating junction temperatures.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

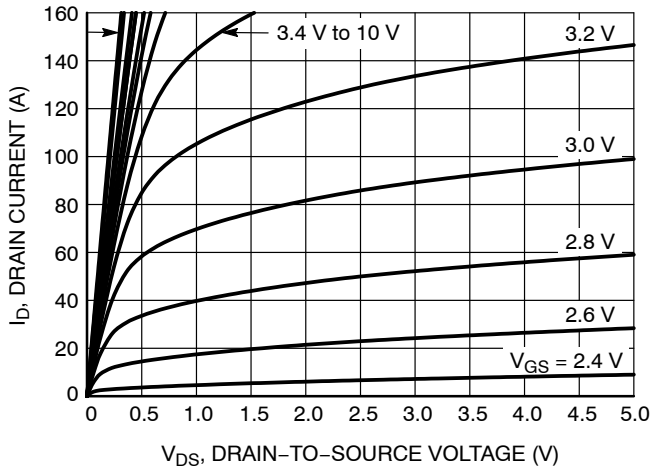


Figure 1. On-Region Characteristics

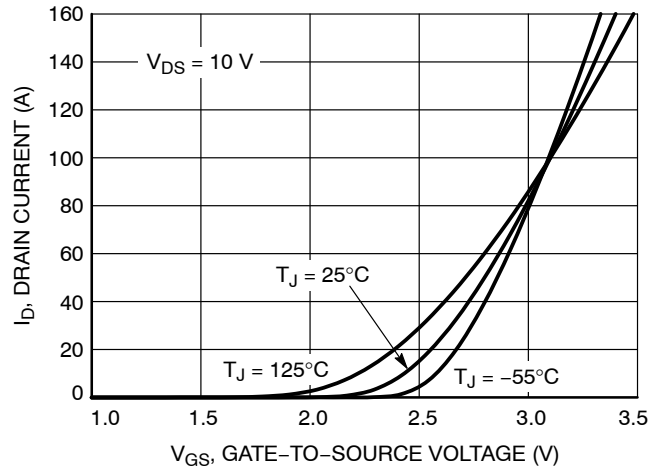


Figure 2. Transfer Characteristics

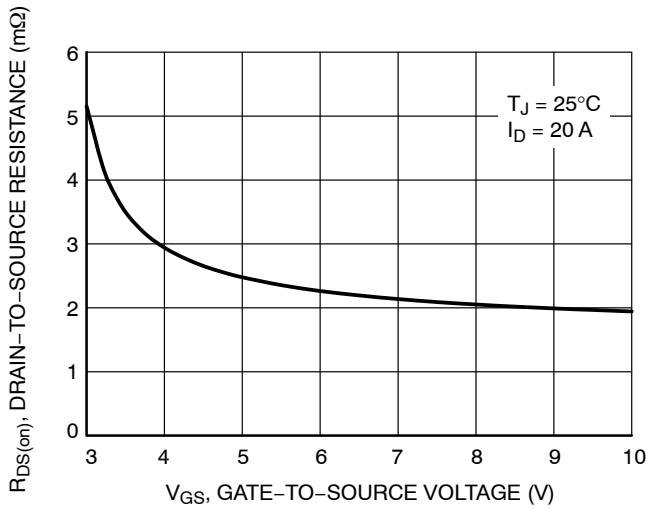


Figure 3. On-Resistance vs. Gate-to-Source Voltage

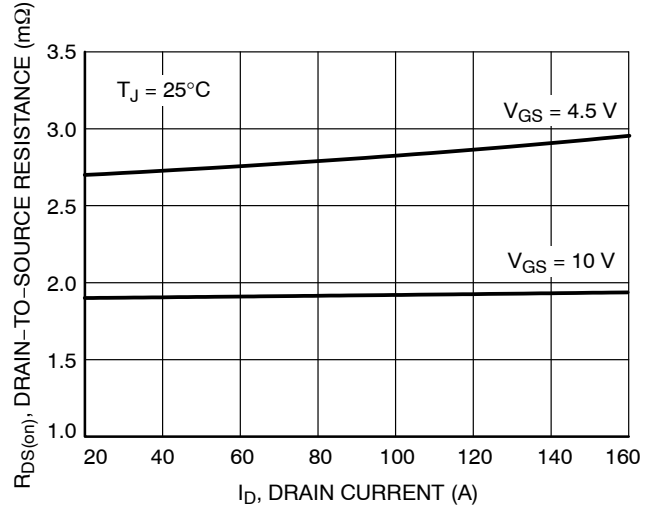


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

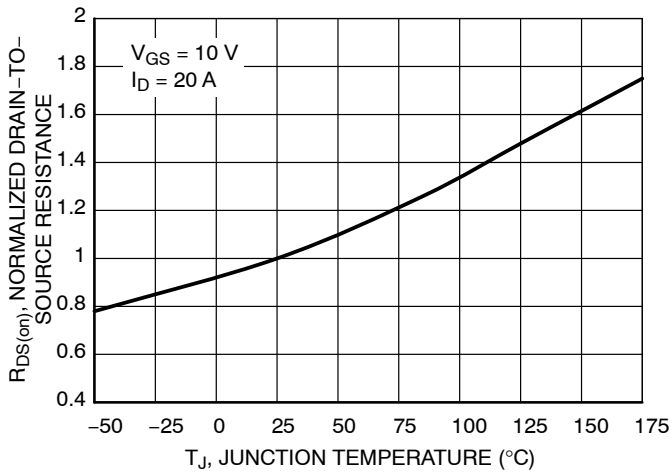


Figure 5. On-Resistance Variation with Temperature

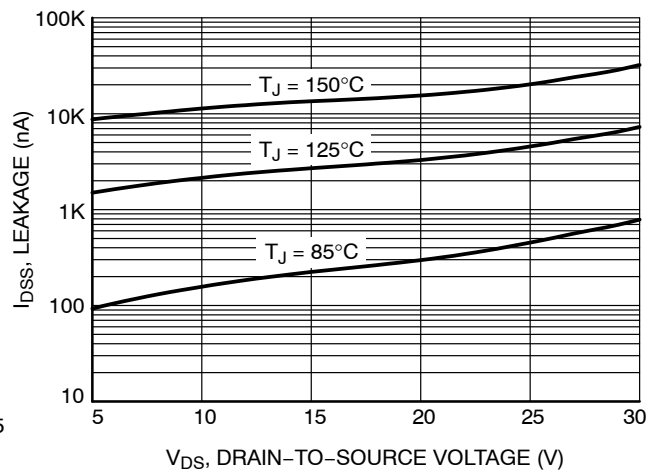


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

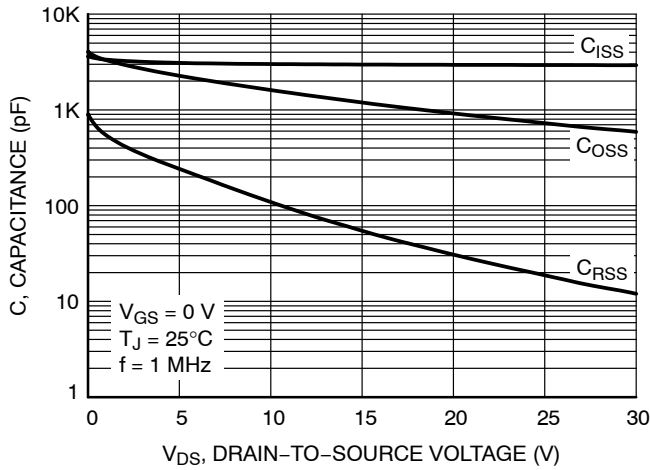


Figure 7. Capacitance Variation

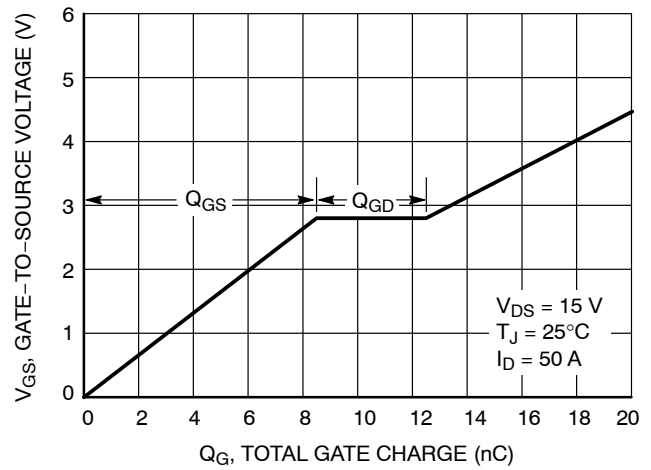


Figure 8. Gate-to-Source vs. Total Charge

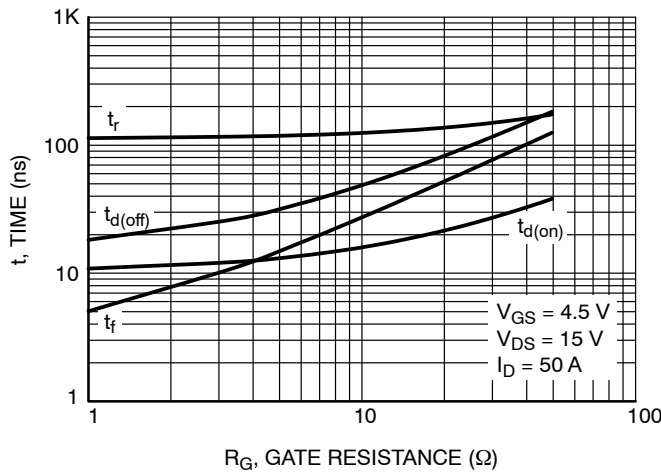


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

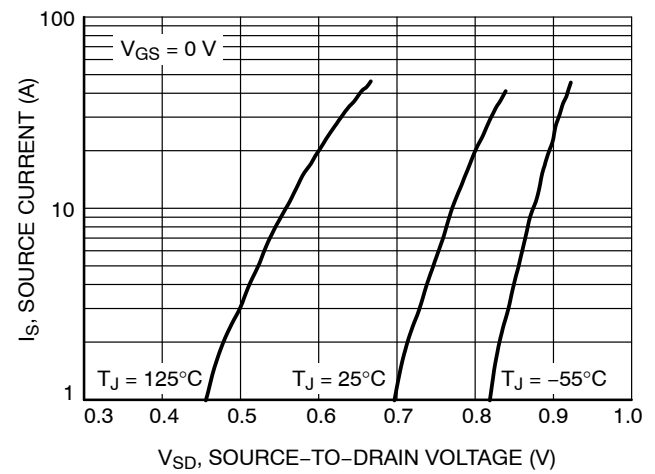


Figure 10. Diode Forward Voltage vs. Current

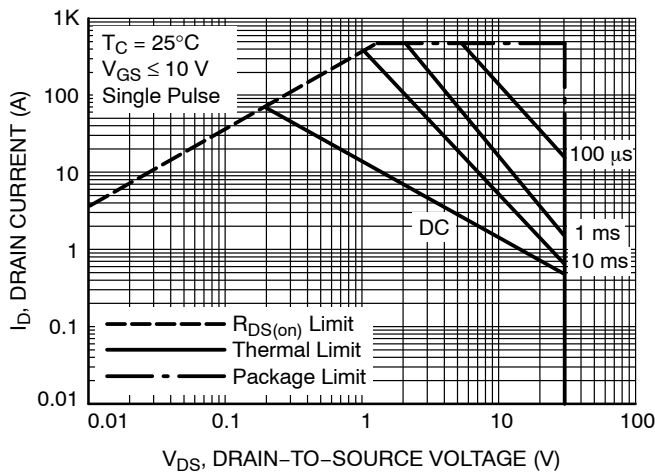


Figure 11. Maximum Rated Forward Biased Safe Operating Area

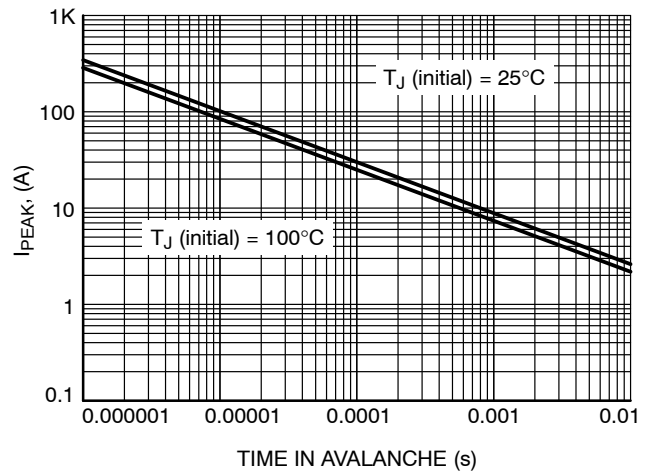


Figure 12. I_{PEAK} vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

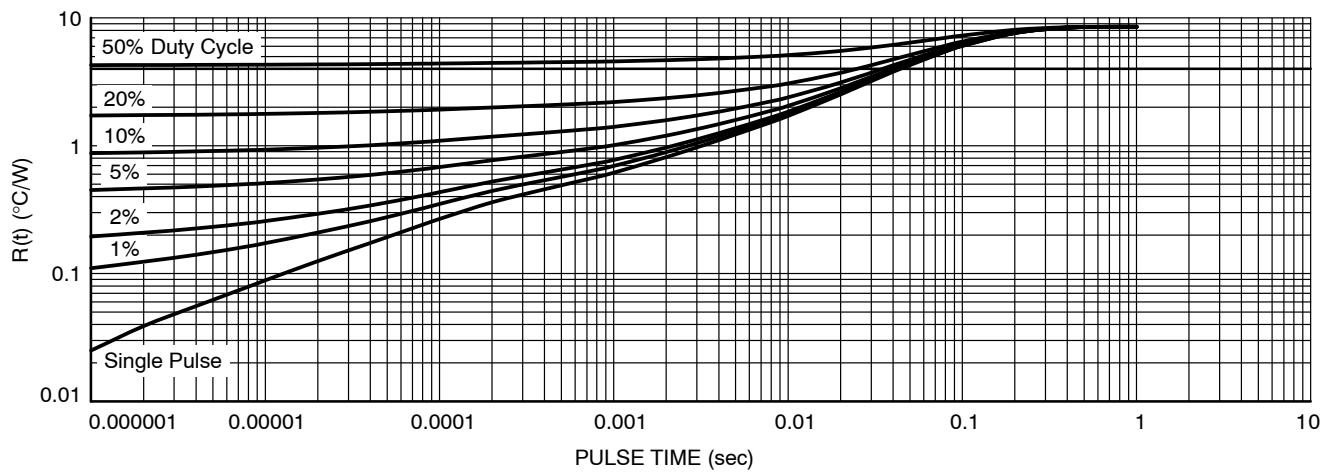


Figure 13. Thermal Characteristics

